SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

Features

- Small surface mounting type
- High reliability

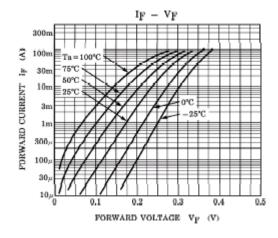
PINNING DESCRIPTION PIN 1 2 Anode Top View Marking Code: "RJ" Simplified outline SOD-323 and symbol

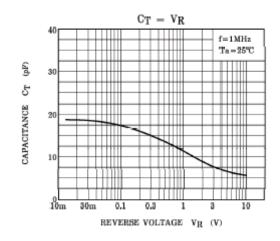
Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	25	V
Reverse Voltage	V_R	20	V
Average Forward Rectified Current	Io	100	mA
Peak Forward Current	I _{FM}	200	mA
Peak Forward Surge Current (60 Hz for 1 Cyc.)	I _{FSM}	1	А
Junction Temperature	T _j	125	°C
Storage Temperature Range	Ts	- 55 to + 125	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Тур.	Max.	Unit
Forward Voltage at I _F = 100 mA	V_{F}	-	0.44	V
Reverse Current at $V_R = 20 \text{ V}$	I _R	-	25	μΑ
Capacitance Between Terminals at $V_R = 10 \text{ V}$, $f = 1 \text{ MHz}$	Ст	8	-	pF







SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)







Dated: 22/04/2008

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323

